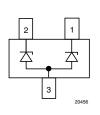


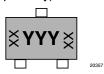
Two-Line ESD Protection in SOT-23





G

MARKING (example only)



YYY = type code (see table below) XX = date code

Н

GSOT05C-

FEATURES

- Two-line ESD-protection device
- ESD-protection acc. IEC 61000-4-2
 - ± 30 kV contact discharge
 - ± 30 kV air discharge
- ESD capability according to AEC-Q101: human body model: class H3B: > 8 kV

please see www.vishay.com/doc?99912

• Material categorization: for definitions of compliance

-18

- Space saving SOT-23 package
- e3 Sn
- AEC-Q101 qualified available



(5-2008) Available

GSOT05C-HG3-18

ORDERING INFORMATION								
	ENVIR	ONMENTAL AN	ID QUALITY CO	ODE	PACKAG	ING CODE		
PART NUMBER (EXAMPLE)	AEC-Q101 QUALIFIED	RoHS-COM LEAD (P	MPLIANT + b)-FREE	TIN PLATED	3K PER 7" REEL (8 mm TAPE),	10K PER 13" REEL (8 mm TAPE),	ORDERING CODE (EXAMPLE)	
(EXAMPLE)	QUALIFIED	STANDARD	GREEN	15K/BOX = MÔQ	5K/BOX = MOQ 10K/BOX = MOQ			
GSOT05C-		E		3	-08		GSOT05C-E3-08	
GSOT05C-			G	3	-08		GSOT05C-G3-08	
GSOT05C-	Н	E		3	-08		GSOT05C-HE3-08	
GSOT05C-	Н		G	3	-08		GSOT05C-HG3-08	
GSOT05C-		E		3		-18	GSOT05C-E3-18	
GSOT05C-			G	3		-18	GSOT05C-G3-18	
GSOT05C-	Н	E		3		-18	GSOT05C-HE3-18	

PACKA	GE DATA							
DEVICE NAME	PACKAGE NAME	TYPE CODE	ENVIRONMENTAL STATUS	WEIGHT	MOLDING COMPOUND FLAMMABILITY RATING	MOISTURE SENSITIVITY LEVEL	SOLDERING CONDITIONS	
GSOT03C	SOT-23	03C	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals	
G301030	301-23	C1G	Green	8.1 mg	OL 94 V-0	(according J-STD-020)	200 C/10 S at terminals	
GSOT04C	SOT-23	04C	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals	
G301040	301-23	C8G	Green	8.1 mg	OL 94 V-0	(according J-STD-020)	200 C/10 S at terminals	
GSOT05C	SOT-23	05C	Standard	8.8 mg	I II Q4 V ₋ 0	UL 94 V-0	MSL level 1	260 °C/10 s at terminals
4301030	301-23	C2G	Green	8.1 mg	OL 94 V-0	(according J-STD-020)	200 O/10 3 at terminais	
GSOT08C	SOT-23	08C	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals	
G30106C	301-23	C3G	Green	8.1 mg	OL 94 V-0	(according J-STD-020)	200 C/10 S at terminals	
GSOT12C	SOT-23	12C	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals	
G301120	301-23	C4G	Green	8.1 mg	OL 94 V-0	(according J-STD-020)	200 C/10 S at terminals	
GSOT15C	SOT-23	15C	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals	
G301130	301-23	C5G	Green	8.1 mg	OL 94 V-0	(according J-STD-020)	200 C/10 s at terminals	
GSOT24C	SOT-23	24C	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals	
G301240	301-23	C6G	Green	8.1 mg	OL 34 V-0	(according J-STD-020)	200 O/TO S at terrillials	
GSOT36C	SOT-23	36C	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals	
3301360	301-23	C7G	Green	8.1 mg	UL 94 V-U	(according J-STD-020)	200 C/10 S at terrifinals	

Rev. 2.5, 07-Mar-16 **1** Document Number: 85824



ABSOLUTE MAXIMUM RATINGS GSOT03C						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Bulling	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	l	30	А		
Peak pulse current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	Іррм	30	Α		
Peak pulse power	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	P _{PP}	369	W		
reak puise power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	ГРР	504	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	\/	± 30	kV		
ESD IIIIIIuliity	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV		
Operating temperature	Junction temperature	T _J	-55 to +150	°C		
Storage temperature		T _{STG}	-55 to +150	°C		

ABSOLUTE MAXIMUM RATINGS GSOT04C						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
B	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	1	30	А		
Peak pulse current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	- Іррм	30	А		
5	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	P _{PP}	429	W		
Peak pulse power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	ГРР	564	W		
ECD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	\/	± 30	kV		
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	± 30	kV		
Operating temperature	Junction temperature	T _J	-55 to +150	°C		
Storage temperature		T _{STG}	-55 to +150	°C		

ABSOLUTE MAXIMUM RATINGS GSOT05C					
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT	
Bud a language	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	I	30	Α	
Peak pulse current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	І _{РРМ}	30 480	Α	
Peak pulse power	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	P _{PP}	480	W	
reak puise power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	ГРР	612	W	
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV	
ESD IIIIIIIIIIII	Air discharge acc. IEC 61000-4-2; 10 pulses	VESD	± 30	kV	
Operating temperature	Junction temperature	T _J	-55 to +150	°C	
Storage temperature		T_{STG}	-55 to +150	°C	



ABSOLUTE MAXIMUM RATINGS GSOT08C						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Bulling	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	I	18	Α		
Peak pulse current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, t_p = 8/20 μ s; single shot	ІРРМ	18 345	Α		
Peak pulse power	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	P _{PP}	345	W		
reak puise power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	ГРР	400	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV		
LSD illillulity	Air discharge acc. IEC 61000-4-2; 10 pulses	VESD	± 30	kV		
Operating temperature	Junction temperature	T _J	-55 to +150	°C		
Storage temperature		T _{STG}	-55 to +150	°C		

ABSOLUTE MAXIMUM RATINGS GSOT12C					
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT	
	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	lane.	12	А	
Peak pulse current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	Іррм	12 312	Α	
Peak pulse power	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, t_p = 8/20 μ s; single shot	P _{PP}	312	W	
i eak puise power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	ı bb	337	W	
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV	
L3D Illillidility	Air discharge acc. IEC 61000-4-2; 10 pulses	VESD	± 30	kV	
Operating temperature	Junction temperature	T _J	-55 to +150	°C	
Storage temperature		T _{STG}	-55 to +150	°C	

ABSOLUTE MAXIMUM RATINGS GSOT15C					
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT	
	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	I	8	А	
Peak pulse current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	ІРРМ	8	А	
	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	D	345	W	
Peak pulse power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	P _{PP} 400	W		
CCD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV	
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV	
Operating temperature	Junction temperature	T _J	-55 to +150	°C	
Storage temperature		T _{STG}	-55 to +150	°C	



ABSOLUTE MAXIMUM RATINGS GSOT24C					
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT	
Dod a large and	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	lan	5	А	
Peak pulse current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	ІРРМ	5 235	А	
Peak pulse power	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	P _{PP}	235	W	
reak puise power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, t _p = 8/20 µs; single shot	Lbb	235	W	
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV	
ESD IIIIIIIIIIIII	Air discharge acc. IEC 61000-4-2; 10 pulses	VESD	± 30	kV	
Operating temperature	Junction temperature	T _J	-55 to +150	°C	
Storage temperature		T _{STG}	-55 to +150	°C	

ABSOLUTE MAXIMUM RATINGS GSOT36C					
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT	
Peak pulse current	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	J	3.5	А	
r eak puise current	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	ІРРМ	3.5	Α	
B	Pin 1 to 3 or pin 2 to 3 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	P _{PP}	248	W	
Peak pulse power	Pin 1 to 2 or pin 2 to 1; pin 3 not connected acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	ГРР	P 252	W	
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	W	± 30	kV	
ESD IIIIIIuiiity	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV	
Operating temperature	Junction temperature	TJ	-55 to +150	°C	
Storage temperature		T _{STG}	-55 to +150	°C	



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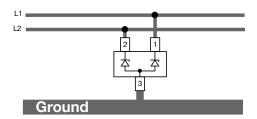
BIAs-MODE (2-line Bidirectional Asymmetrical protection mode)

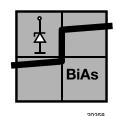
With the GSOTxxC two signal- or data-lines (L1, L2) can be protected against voltage transients. With pin 3 connected to ground and pin 1 and pin 2 connected to a signal- or data-line which has to be protected. As long as the voltage level on the data- or signal-line is between 0 V (ground level) and the specified Maximum Reverse Working Voltage (V_{RWM}) the protection diode between pin 2 and pin 3 and between pin 1 and pin 3 offers a high isolation to the ground line. The protection device behaves like an open switch.

As soon as any positive transient voltage signal exceeds the breakdown voltage level of the protection diode, the diode becomes conductive and shorts the transient current to ground. Now the protection device behaves like a closed switch. The Clamping Voltage (V_C) is defined by the breakdown voltage (V_{BR}) level plus the voltage drop at the series impedance (resistance and inductance) of the protection diode.

Any negative transient signal will be clamped accordingly. The negative transient current is flowing in the forward direction through the protection diode. The low Forward Voltage (V_F) clamps the negative transient close to the ground level.

Due to the different clamping levels in forward and reverse direction the GSOTxxC clamping behavior is Bidirectional and Asymmetrical (BiAs).

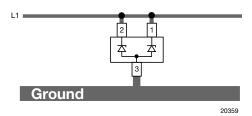




If a higher surge current or peak pulse current (I_{PP}) is needed, both protection diodes in the GSOTxxC can also be used in parallel in order to "double" the performance.

This offers:

- double surge power = double peak pulse current (2 x I_{PPM})
- half of the line inductance = reduced clamping voltage
- half of the line resistance = reduced clamping voltage
- double line capacitance (2 x C_D)
- double reverse leakage current (2 x I_R)



ELECTRICAL CHARACTERISTICS GSOT03C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3						
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	3.3	V
Reverse voltage	at I _R = 100 μA	V_R	3.3	-	-	V
Reverse current	at V _R = 3.3 V	I _R	-	-	100	μΑ
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	4.0	4.6	5.5	V
Davaga alamaina valtara	at I _{PP} = 1 A	V	-	5.7	7.5	V
Reverse clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _C	-	10	12.3	V
Famusard alamaina valtaga	at I _{PP} = 1 A	V	-	1	1.2	V
Forward clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _F	-	4.5	-	V
Canacitanas	at V _R = 0 V; f = 1 MHz	(-	420	600	pF
Capacitance	at V _R = 1.6 V; f = 1 MHz	- C _D	-	260	-	pF



ELECTRICAL CHARACTERISTICS GSOT04C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3							
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines	
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	=	-	4	V	
Reverse voltage	at I _R = 20 μA	V_R	4	-	-	V	
Reverse current	at V _R = 4 V	I _R	-	-	20	μΑ	
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	5	6.1	7	V	
Poverse elemning voltage	at I _{PP} = 1 A	V	-	7.5	9	V	
Reverse clamping voltage	at I _{PP} = I _{PPM} = 30 A	- V _C	-	11.2	14.3	V	
Forward elemning voltage	at I _{PP} = 1 A	V	-	1	1.2	V	
Forward clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _F	-	4.5	-	V	
Canacitanas	at V _R = 0 V; f = 1 MHz		-	310	450	pF	
Capacitance	at V _R = 2 V; f = 1 MHz	- C _D	-	200	-	pF	

ELECTRICAL CHARACTERISTICS GSOT05C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines		
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	5	V		
Reverse voltage	at I _R = 10 μA	V _R	5	-	-	V		
Reverse current	at V _R = 5 V	I _R	-	-	10	μΑ		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	6	6.8	8	V		
Payaraa alampina valtaga	at I _{PP} = 1 A	V-	-	7	8.7	V		
Reverse clamping voltage	at I _{PP} = I _{PPM} = 30 A	- V _C	-	12	16	V		
Forward alamaina voltago	at I _{PP} = 1 A	V	-	1	1.2	V		
Forward clamping voltage	ge at I _{PP} = I _{PPM} = 30 A	-	4.5	-	V			
Canacitanas	at V _R = 0 V; f = 1 MHz		-	260	350	pF		
Capacitance	at V _R = 2.5 V; f = 1 MHz	- C _D	-	150	-	pF		

ELECTRICAL CHARACTERISTICS GSOT08C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines		
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	8	V		
Reverse voltage	at I _R = 5 μA	V_R	8	-	-	V		
Reverse current	at V _R = 8 V	I _R	-	-	5	μΑ		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	9	10	11	V		
Poverse elemning voltage	at I _{PP} = 1 A	V _C	-	10.7	13	V		
Reverse clamping voltage	at I _{PP} = I _{PPM} = 18 A	v _C	-	15.2	19.2	V		
Forward elemping voltage	at I _{PP} = 1 A	\/	-	1	1.2	V		
Forward clamping voltage	at I _{PP} = I _{PPM} = 18 A	V _F	-	3	-	V		
Canacitanas	at $V_R = 0 V$; $f = 1 MHz$	0	-	160	250	pF		
Capacitance	at V _R = 4 V; f = 1 MHz	- C _D	-	80	-	pF		



ELECTRICAL CHARACTERISTICS GSOT12C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines		
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	12	V		
Reverse voltage	at I _R = 1 μA	V_R	12	-	-	V		
Reverse current	at V _R = 12 V	I _R	-	-	1	μA		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	13.5	15	16.5	V		
Boyeres elemning veltage	at I _{PP} = 1 A	V	-	15.4	18.7	V		
Reverse clamping voltage	at I _{PP} = I _{PPM} = 12 A	V _C	-	21.2	26	V		
Forward elemping voltage	at I _{PP} = 1 A	V _F	-	1	1.2	V		
Forward clamping voltage	at I _{PP} = I _{PPM} = 12 A	VF	-	2.2	-	V		
Canacitanas	at V _R = 0 V; f = 1 MHz	_	-	115	150	pF		
Capacitance	at V _R = 6 V; f = 1 MHz	- C _D	-	50	-	pF		

ELECTRICAL CHARACTERISTICS GSOT15C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines		
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	15	V		
Reverse voltage	at I _R = 1 μA	V_R	15	-	-	V		
Reverse current	at V _R = 15 V	I _R	-	-	1	μA		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	16.5	18	20	V		
Poverse elemning voltage	at I _{PP} = 1 A	.,	-	19.4	23.5	V		
Reverse clamping voltage	at I _{PP} = I _{PPM} = 8 A	V _C	-	24.8	28.8	V		
Forward clamping voltage	at I _{PP} = 1 A	V _F	-	1	1.2	V		
Forward clamping voltage	at I _{PP} = I _{PPM} = 8 A	VF	-	1.8	-	V		
Capacitance	at $V_R = 0 V$; $f = 1 MHz$	- C _D	-	90	120	pF		
Оараспансе	at V _R = 7.5 V; f = 1 MHz		-	35	-	pF		

ELECTRICAL CHARACTERISTICS GSOT24C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 3 or pin 2 to pin 3								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines		
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	24	V		
Reverse voltage	at I _R = 1 μA	V_R	24	-	-	V		
Reverse current	at V _R = 24 V	I _R	-	-	1	μΑ		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	27	30	33	V		
Deverse elemning veltage	at I _{PP} = 1 A	.,	-	34	41	V		
Reverse clamping voltage	at I _{PP} = I _{PPM} = 5 A	V _C	-	41	47	V		
Converd elemening veltage	at I _{PP} = 1 A		-	1	1.2	V		
Forward clamping voltage	at I _{PP} = I _{PPM} = 5 A	V _F	-	1.4	-	V		
Canacitanas	at V _R = 0 V; f = 1 MHz		-	65	80	pF		
Capacitance	at V _R = 12 V; f = 1 MHz	- C _D	-	20	-	pF		

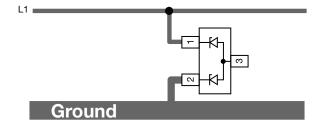


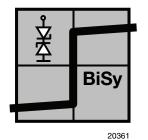
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	2	lines
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	36	V
Reverse voltage	at I _R = 1 μA	V_R	36	-	-	V
Reverse current	at V _R = 36 V	I _R	-	-	1	μA
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	39	43	47	V
Deverse elemping veltage	at I _{PP} = 1 A	V	-	49	60	V
Reverse clamping voltage	at I _{PP} = I _{PPM} = 3.5 A	V _C	-	59	71	V
Famous alamatica college	at I _{PP} = 1 A	W	-	1	1.2	V
Forward clamping voltage	at I _{PP} = I _{PPM} = 3.5 A	V _F	-	1.3	-	V
Ossasitansa	at V _R = 0 V; f = 1 MHz	- C _D	-	52	65	pF
Capacitance	at V _B = 18 V; f = 1 MHz		-	12	_	pF

BISy-MODE (1-line bidirectional symmetrical protection mode)

If a bipolar symmetrical protection device is needed the GSOTxxC can also be used as a single line protection device. Therefore pin 1 has to be connected to the signal- or data-line (L1) and pin 2 to ground (or vice versa). Pin 3 must not be connected. Positive and negative voltage transients will be clamped in the same way. The clamping current through the GSOTxxC passes one diode in forward direction and the other one in reverse direction. The clamping voltage (V_C) is defined by the breakthrough voltage (V_{BR}) level of one diode plus the forward voltage of the other diode plus the voltage drop at the series impedances (resistances and inductances) of the protection device.

Due to the same clamping levels in positive and negative direction the GSOTxxC voltage clamping behaviour is bidirectional and symmetrical (BiSy).





ELECTRICAL CHARACTERISTICS GSOT03C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines		
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	3.8	V		
Reverse voltage	at I _R = 100 μA	V_R	3.8	-	-	V		
Reverse current	at V _R = 3.8 V	I _R	-	-	100	μΑ		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	4.5	5.3	6.2	V		
Reverse clamping voltage	at I _{PP} = 1 A	V _C	-	7	8.4	V		
neverse clamping voltage	at I _{PP} = I _{PPM} = 30 A	v _C	-	14	16.8	V		
Capacitance	at V _R = 0 V; f = 1 MHz	- C _D	-	210	300	pF		
Capacitaric e	at V _R = 1.6 V; f = 1 MHz		-	190	-	pF		



ELECTRICAL CHARACTERISTICS GSOT04C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines		
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	4.5	V		
Reverse voltage	at I _R = 20 μA	V_R	4.5	-	-	V		
Reverse current	at V _R = 4.5 V	I _R	-	-	20	μA		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	5.5	6.8	7.7	V		
Reverse clamping voltage	at I _{PP} = 1 A	V _C	-	7.5	9	V		
heverse clamping voltage	at I _{PP} = I _{PPM} = 30 A	v _C	-	15.7	18.8	V		
Constitutes	at V _R = 0 V; f = 1 MHz	C _D	-	155	225	pF		
Capacitance	at V _R = 2 V; f = 1 MHz		-	135	-	pF		

ELECTRICAL CHARACTERISTICS GSOT05C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines		
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	5.5	V		
Reverse voltage	at I _R = 10 μA	V_{R}	5.5	-	-	V		
Reverse current	at V _R = 5.5 V	I _R	-	-	10	μΑ		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	6.5	7.5	8.7	V		
Reverse clamping voltage	at I _{PP} = 1 A	V _C	-	8.1	9.7	V		
heverse clamping voltage	at I _{PP} = I _{PPM} = 30 A	v _C	-	17	20.4	V		
Capacitance	at V _R = 0 V; f = 1 MHz	- C _D	-	130	175	pF		
	at V _R = 4 V; f = 1 MHz		-	100	-	pF		

ELECTRICAL CHARACTERISTICS GSOT08C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines		
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	8.5	V		
Reverse voltage	at I _R = 5 μA	V_R	8.5	-	-	V		
Reverse current	at V _R = 8.5 V	I _R	-	-	5	μA		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	9.5	10.7	11.7	V		
Payaraa alamaina valtaga	at I _{PP} = 1 A	V _C	-	11.7	14	V		
Reverse clamping voltage	at I _{PP} = I _{PPM} = 18 A	v _C	-	18.5	22.2	V		
Capacitance	at V _R = 0 V; f = 1 MHz	- C _D	-	80	125	pF		
Сараспансе	at V _R = 4 V; f = 1 MHz	C_{D}	ı	60	-	pF		

ELECTRICAL CHARACTERISTICS GSOT12C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines		
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	12.5	V		
Reverse voltage	at I _R = 1 μA	V_R	12.5	-	-	V		
Reverse current	at V _R = 12.5 V	I _R	-	-	1	μA		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	13.5	15.7	16.5	V		
Reverse clamping voltage	at I _{PP} = 1 A	V _C	-	16.4	19.7	V		
heverse clamping voltage	at I _{PP} = I _{PPM} = 12 A	VC	-	23.4	28.1	V		
Capacitance	at V _R = 0 V; f = 1 MHz	- C _D	-	58	75	pF		
Сараспансе	at V _R = 7.5 V; f = 1 MHz		-	36	-	pF		



ELECTRICAL CHARACTERISTICS GSOT15C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	=	1	lines		
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	15.5	V		
Reverse voltage	at I _R = 1 μA	V_R	15.5	-	-	V		
Reverse current	at V _R = 15.5 V	I _R	-	-	1	μA		
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	17	18.7	20.7	V		
Reverse clamping voltage	at I _{PP} = 1 A	V _C	-	20.4	24.5	V		
neverse clamping voltage	at I _{PP} = I _{PPM} = 8 A	VC	-	26.6	30.6	V		
0	at V _R = 0 V; f = 1 MHz	- C _D	-	45	60	pF		
Capacitance	at V _R = 7.5 V; f = 1 MHz		-	25	-	pF		

ELECTRICAL CHARACTERISTICS GSOT24C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected									
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT			
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines			
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	24.5	V			
Reverse voltage	at I _R = 1 μA	V_R	24.5	-	-	V			
Reverse current	at V _R = 24.5 V	I _R	-	-	1	μA			
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	27.5	30.7	33.7	V			
Reverse clamping voltage	at I _{PP} = 1 A	- V _C	-	34	41	V			
	at I _{PP} = I _{PPM} = 5 A		-	40	48	V			
Capacitance	at V _R = 0 V; f = 1 MHz	- C _D	-	33	40	pF			
	at V _R = 12 V; f = 1 MHz		-	18	-	pF			

ELECTRICAL CHARACTERISTICS GSOT36C (T _{amb} = 25 °C unless otherwise specified) between pin 1 to pin 2 or pin 2 to pin1; pin 3 not connected									
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT			
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines			
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	36.5	V			
Reverse voltage	at I _R = 1 μA	V_R	36.5	-	-	V			
Reverse current	at V _R = 36.5 V	I _R	-	-	1	μA			
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	39.5	43.7	47.7	V			
Reverse clamping voltage	at I _{PP} = 1 A	V _C	-	50	60	V			
	at I _{PP} = I _{PPM} = 3.5 A		-	60	72	V			
Capacitance	at $V_R = 0 V$; $f = 1 MHz$	- C _D	-	26	33	pF			
	at V _R = 18 V; f = 1 MHz		-	10	-	pF			



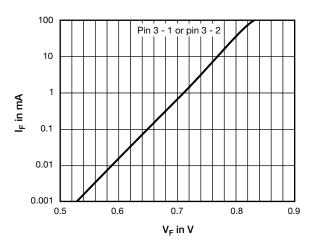


Fig. 1 - Typical Forward Current I_F vs. Forward Voltage V_F

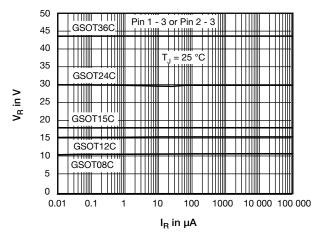


Fig. 2 - Typical Reverse Voltage V_R vs. Reverse Current I_R

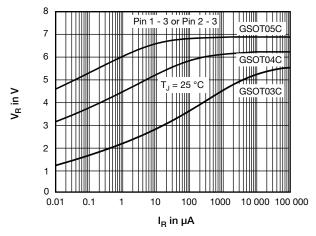
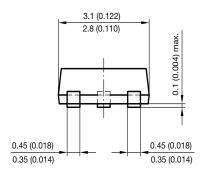
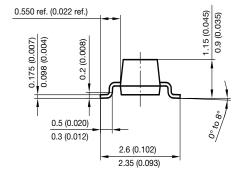


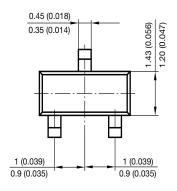
Fig. 3 - Typical Reverse Voltage V_{R} vs. Reverse Current I_{R}

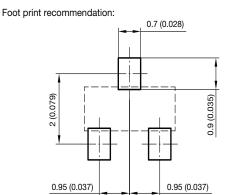


PACKAGE DIMENSIONS in millimeters (inches): SOT-23

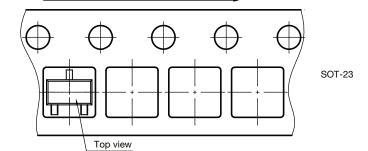








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Orientation in carrier tape SOT-23 S8-V-3929.01-006 (4) 04.02.2010 22607

Unreeling direction



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